

Please amend claims 44-48, 51-54 and 70 in the following
rewritten forms:

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G1*
-- 44. (Amended) An active matrix type display device comprising:

a substrate;

a pixel circuit formed over said substrate for switching
pixels of said display device;

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a driver circuit comprising thin film transistors adhered
to said substrate by a resin;

a passivation film covering said driver circuit, said
passivation film having a contact hole to allow an electrical
connection between at least one of said thin film transistors
and said pixel circuit;

a wiring formed over said passivation film to form said
electrical connection; and

a sealing member over said substrate, wherein said sealing
member encloses said pixel circuit and said driver circuit.

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45. (Amended) A display device according to claim 44 wherein
said passivation film comprises at least two layers having
different etching rates, and said contact hole has a tapered
configuration.

*F2
contd.* 46. (Amended) An active matrix type display device according to claim 44 wherein each of said thin film transistors has a channel region comprising crystalline silicon.

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contd.* 47. (Amended) An active matrix type display device according to claim 44 wherein said substrate comprises a plastic.

48. (Amended) An active matrix type display device according to claim 44 wherein said driver circuit is overlapped by another substrate opposed to said substrate.

51. (Amended) An active matrix type display device according to claim 44 wherein said passivation film comprises polyimide.

14 52. (Amended) An active matrix type display device according to claim 44 wherein said passivation film comprises silicon oxide.

53. (Amended) An active matrix type display device according to claim 44 wherein said pixel circuit comprises a first plurality of transparent conductive films and a second plurality of transparent conductive films extending across said first plurality of transparent conductive films.

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comd.
54.(Amended) An active matrix type display device according
to claim 44 wherein said pixel circuit comprises pixel
electrodes connected to TFTs.

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70.(Amended) An active matrix type display device according
to claim 44 wherein said driver circuit is formed from a stick
substrate separate from said substrate.--

Please add new claims 72-104 as follows.

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--72.(New) An active matrix type display device comprising:
a pixel circuit formed over a substrate for switching
pixels of said display device;
a driver circuit comprising thin film transistors adhered
to said substrate by a resin;
an insulating film formed over said driver circuit; and
a wiring formed over said insulating film, wherein said
driver circuit is electrically connected to said pixel circuit
through said wiring.

73.(New) An active matrix type display device according to
claim 72 wherein each of said thin film transistors has a
channel region comprising crystalline silicon.

74. (New) An active matrix type display device according to claim 72 wherein said substrate comprises a plastic.

75. (New) An active matrix type display device according to claim 72 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

76. (New) An active matrix type display device according to claim 72 wherein said driver circuit is formed from a stick substrate separate from said substrate.

77. (New) An active matrix type display device according to claim 72 wherein said display device is a liquid crystal display device.

78. (New) An active matrix type display device comprising:
a pixel circuit formed over a substrate for switching pixels of said display device;
a driver circuit comprising thin film transistors adhered to said substrate by a resin;
an insulating film formed over said driver circuit; and

a wiring comprising indium tin oxide formed over said insulating film, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

79. (New) An active matrix type display device according to claim 78 wherein each of said thin film transistors has a channel region comprising crystalline silicon.

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cont.
80. (New) An active matrix type display device according to claim 78 wherein said substrate comprises a plastic.

81. (New) An active matrix type display device according to claim 78 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

82. (New) An active matrix type display device according to claim 78 wherein said driver circuit is formed from a stick substrate separate from said substrate.

83. (New) An active matrix type display device according to claim 78 wherein said display device is a liquid crystal display device.

84. (New) An active matrix type display device comprising:
a pixel circuit formed over a substrate for switching
pixels of said display device;
a driver circuit comprising thin film transistors adhered
to said substrate by a resin;
an insulating film formed over said driver circuit; and
a wiring comprising indium tin oxide formed over said
insulating film and extending on a same layer as (said resin),
wherein said driver circuit is electrically connected to said
pixel circuit through said wiring.

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contd.

85. (New) An active matrix type display device according to
claim 84 wherein each of said thin film transistors has a
channel region comprising crystalline silicon.

86. (New) An active matrix type display device according to
claim 84 wherein said substrate comprises a plastic.

87. (New) An active matrix type display device according to
claim 84 wherein said insulating film comprises at least one
selected from the group consisting of polyimide and silicon
oxide.

88. (New) An active matrix type display device according to claim 84 wherein said driver circuit is formed from a stick substrate separate from said substrate.

89. (New) An active matrix type display device according to claim 84 wherein said display device is a liquid crystal display device.

90. (New) An active matrix type display device comprising:

a pixel circuit formed over a substrate for switching pixels of said display device;

a resin formed over said substrate;

a base film on said resin;

a semiconductor layer on said base film;

a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;

at least one of source and drain electrodes connected to said semiconductor layer;

an insulating film formed over at least said semiconductor layer and said gate electrode; and

a wiring formed over said insulating film, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

91. (New) An active matrix type display device according to claim 90 wherein said semiconductor layer comprises crystalline silicon.

92. (New) An active matrix type display device according to claim 90 wherein said substrate comprises a plastic.

93.(New) An active matrix type display device according to claim 90 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

94.(New) An active matrix type display device according to claim 90 wherein said display device is a liquid crystal display device.

95.(New) An active matrix type display device comprising:
a pixel circuit formed over a substrate for switching pixels of said display device;

a resin formed over said substrate;

a base film on said resin;

a semiconductor layer on said base film;

a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;

at least one of source and drain electrodes connected to said semiconductor layer;

an insulating film formed over at least said semiconductor layer and said gate electrode; and

a wiring comprising indium tin oxide formed over said insulating film, wherein said at least one of said source and

drain electrodes is electrically connected to said pixel circuit through said wiring.

96. (New) An active matrix type display device according to claim 95 wherein said semiconductor layer comprises crystalline silicon.

97. (New) An active matrix type display device according to claim 95 wherein said substrate comprises a plastic.

98. (New) An active matrix type display device according to claim 95 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

99. (New) An active matrix type display device according to claim 95 wherein said display device is a liquid crystal display device.

100. (New) An active matrix type display device comprising:
a pixel circuit formed over a substrate for switching pixels of said display device;
a resin formed over said substrate;
a base film on said resin;

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a semiconductor layer on said base film;
a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;
at least one of source and drain electrodes connected to said semiconductor layer;
an insulating film formed over at least said semiconductor layer and said gate electrode; and
a wiring comprising indium tin oxide formed over said insulating film and extending on a same layer as said resin, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

101.(New) An active matrix type display device according to claim 100 wherein said semiconductor layer comprises crystalline silicon.

102.(New) An active matrix type display device according to claim 100 wherein said substrate comprises a plastic.

103.(New) An active matrix type display device according to claim 100 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

104.(New) An active matrix type display device according to
claim 100 wherein said display device is a liquid crystal
display device.--
